

Digital Transistors (BRT)

R1 = 10 kΩ, R2 = 47 kΩ

MUN2214, MMUN2214L, MUN5214, DTC114YE, DTC114YM3, NSBC114YF3

NPN Transistors with Monolithic Bias Resistor Network

This series of digital transistors is designed to replace a single device and its external resistor bias network. The Bias Resistor Transistor (BRT) contains a single transistor with a monolithic bias network consisting of two resistors; a series base resistor and a base-emitter resistor. The BRT eliminates these individual components by integrating them into a single device. The use of a BRT can reduce both system cost and board space.

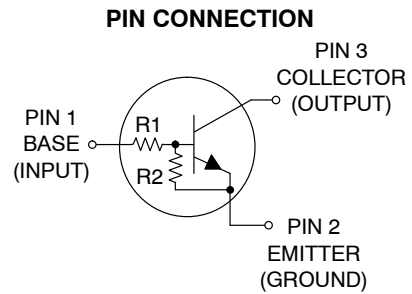
Features

- Simplifies Circuit Design
- Reduces Board Space
- Reduces Component Count
- S and NSV Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC-Q101 Qualified and PPAP Capable
- These Devices are Pb-Free, Halogen Free/BFR Free and are RoHS Compliant

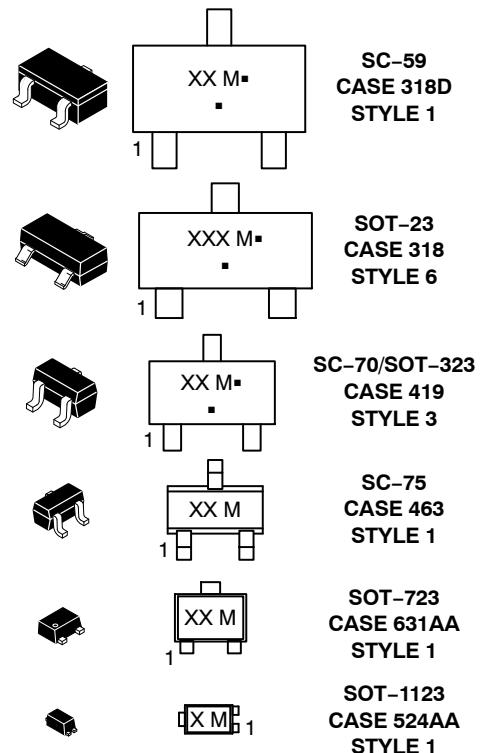
MAXIMUM RATINGS (T_A = 25 °C)

Rating	Symbol	Max	Unit
Collector-Base Voltage	V _{CBO}	50	Vdc
Collector-Emitter Voltage	V _{CEO}	50	Vdc
Collector Current - Continuous	I _C	100	mAdc
Input Forward Voltage	V _{IN(fwd)}	40	Vdc
Input Reverse Voltage	V _{IN(rev)}	6	Vdc

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.



MARKING DIAGRAM



XXX = Specific Device Code
M = Date Code*
▪ = Pb-Free Package

(Note: Microdot may be in either location)

*Date Code orientation may vary depending upon manufacturing location.

ORDERING INFORMATION

See detailed ordering, marking, and shipping information in the package dimensions section on page 2 of this data sheet.

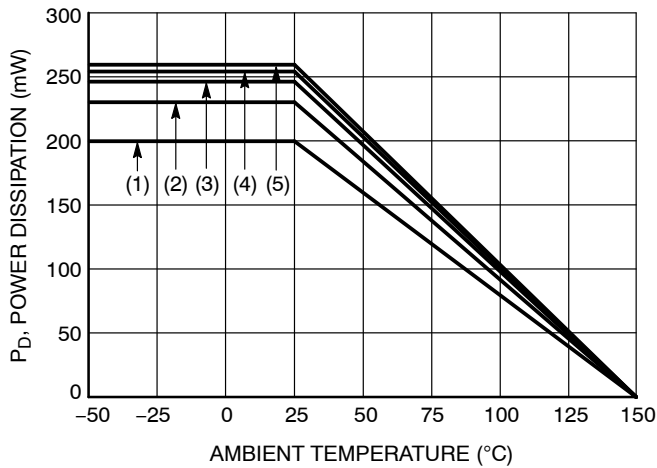
MUN2214, MMUN2214L, MUN5214, DTC114YE, DTC114YM3, NSBC114YF3

Table 1. ORDERING INFORMATION

Device	Part Marking	Package	Shipping†
MUN2214T1G, SMUN2214T1G*	8D	SC-59 (Pb-Free)	3000 / Tape & Reel
MUN2214T3G, SMUN2214T3G*	8D	SC-59 (Pb-Free)	10000 / Tape & Reel
MMUN2214LT1G, SMMUN2214LT1G*	A8D	SOT-23 (Pb-Free)	3000 / Tape & Reel
MUN5214T1G, SMUN5214T1G*	8D	SC-70/SOT-323 (Pb-Free)	3000 / Tape & Reel
DTC114YET1G, SDTC114YET1G	8D	SC-75 (Pb-Free)	3000 / Tape & Reel
DTC114YM3T5G, NSVDTC114YM3T5G*	8D	SOT-723 (Pb-Free)	8000 / Tape & Reel
NSBC114YF3T5G	J	SOT-1123 (Pb-Free)	8000 / Tape & Reel

†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

*S and NSV Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC-Q101 Qualified and PPAP Capable.



- (1) SC-75 and SC-70/SOT-323; Minimum Pad
- (2) SC-59; Minimum Pad
- (3) SOT-23; Minimum Pad
- (4) SOT-1123; 100 mm², 1 oz. copper trace
- (5) SOT-723; Minimum Pad

Figure 1. Derating Curve

MUN2214, MMUN2214L, MUN5214, DTC114YE, DTC114YM3, NSBC114YF3

Table 2. THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
THERMAL CHARACTERISTICS (SC-59) (MUN2214)			
Total Device Dissipation $T_A = 25^\circ\text{C}$	P_D	230	mW
Derate above 25°C		338	$\text{mW}/^\circ\text{C}$
		1.8	
		2.7	
Thermal Resistance, Junction to Ambient	$R_{\theta JA}$	540	$^\circ\text{C}/\text{W}$
		370	
Thermal Resistance, Junction to Lead	$R_{\theta JL}$	264	$^\circ\text{C}/\text{W}$
		287	
Junction and Storage Temperature Range	T_J, T_{stg}	-55 to +150	$^\circ\text{C}$
THERMAL CHARACTERISTICS (SOT-23) (MMUN2214L)			
Total Device Dissipation $T_A = 25^\circ\text{C}$	P_D	246	mW
Derate above 25°C		400	$\text{mW}/^\circ\text{C}$
		2.0	
		3.2	
Thermal Resistance, Junction to Ambient	$R_{\theta JA}$	508	$^\circ\text{C}/\text{W}$
		311	
Thermal Resistance, Junction to Lead	$R_{\theta JL}$	174	$^\circ\text{C}/\text{W}$
		208	
Junction and Storage Temperature Range	T_J, T_{stg}	-55 to +150	$^\circ\text{C}$
THERMAL CHARACTERISTICS (SC-70/SOT-323) (MUN5214)			
Total Device Dissipation $T_A = 25^\circ\text{C}$	P_D	202	mW
Derate above 25°C		310	$\text{mW}/^\circ\text{C}$
		1.6	
		2.5	
Thermal Resistance, Junction to Ambient	$R_{\theta JA}$	618	$^\circ\text{C}/\text{W}$
		403	
Thermal Resistance, Junction to Lead	$R_{\theta JL}$	280	$^\circ\text{C}/\text{W}$
		332	
Junction and Storage Temperature Range	T_J, T_{stg}	-55 to +150	$^\circ\text{C}$
THERMAL CHARACTERISTICS (SC-75) (DTC114YE)			
Total Device Dissipation $T_A = 25^\circ\text{C}$	P_D	200	mW
Derate above 25°C		300	$\text{mW}/^\circ\text{C}$
		1.6	
		2.4	
Thermal Resistance, Junction to Ambient	$R_{\theta JA}$	600	$^\circ\text{C}/\text{W}$
		400	
Junction and Storage Temperature Range	T_J, T_{stg}	-55 to +150	$^\circ\text{C}$
THERMAL CHARACTERISTICS (SOT-723) (DTC114YM3)			
Total Device Dissipation $T_A = 25^\circ\text{C}$	P_D	260	mW
Derate above 25°C		600	$\text{mW}/^\circ\text{C}$
		2.0	
		4.8	
Thermal Resistance, Junction to Ambient	$R_{\theta JA}$	480	$^\circ\text{C}/\text{W}$
		205	
Junction and Storage Temperature Range	T_J, T_{stg}	-55 to +150	$^\circ\text{C}$

- FR-4 @ Minimum Pad.
- FR-4 @ 1.0 x 1.0 Inch Pad.
- FR-4 @ 100 mm², 1 oz. copper traces, still air.
- FR-4 @ 500 mm², 1 oz. copper traces, still air.

Table 2. THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
THERMAL CHARACTERISTICS (SOT-1123) (NSBC114YF3)			
Total Device Dissipation $T_A = 25^\circ\text{C}$ Derate above 25°C	(Note 3) (Note 4) (Note 3) (Note 4) P_D	254 297 2.0 2.4	mW mW/ $^\circ\text{C}$
Thermal Resistance, Junction to Ambient	(Note 3) (Note 4) $R_{\theta JA}$	493 421	$^\circ\text{C}/\text{W}$
Thermal Resistance, Junction to Lead	(Note 3) $R_{\theta JL}$	193	$^\circ\text{C}/\text{W}$
Junction and Storage Temperature Range	T_J, T_{stg}	-55 to +150	$^\circ\text{C}$

- FR-4 @ Minimum Pad.
- FR-4 @ 1.0 x 1.0 Inch Pad.
- FR-4 @ 100 mm², 1 oz. copper traces, still air.
- FR-4 @ 500 mm², 1 oz. copper traces, still air.

Table 3. ELECTRICAL CHARACTERISTICS ($T_A = 25^\circ\text{C}$, unless otherwise noted)

Characteristic	Symbol	Min	Typ	Max	Unit
OFF CHARACTERISTICS					
Collector-Base Cutoff Current ($V_{CB} = 50\text{ V}, I_E = 0$)	I_{CBO}	-	-	100	nAdc
Collector-Emitter Cutoff Current ($V_{CE} = 50\text{ V}, I_B = 0$)	I_{CEO}	-	-	500	nAdc
Emitter-Base Cutoff Current ($V_{EB} = 6.0\text{ V}, I_C = 0$)	I_{EBO}	-	-	0.2	mAdc
Collector-Base Breakdown Voltage ($I_C = 10\ \mu\text{A}, I_E = 0$)	$V_{(BR)CBO}$	50	-	-	Vdc
Collector-Emitter Breakdown Voltage (Note 5) ($I_C = 2.0\text{ mA}, I_B = 0$)	$V_{(BR)CEO}$	50	-	-	Vdc
ON CHARACTERISTICS					
DC Current Gain (Note 5) ($I_C = 5.0\text{ mA}, V_{CE} = 10\text{ V}$)	h_{FE}	80	140	-	
Collector - Emitter Saturation Voltage (Note 5) ($I_C = 10\text{ mA}, I_B = 0.3\text{ mA}$)	$V_{CE(sat)}$	-	-	0.25	Vdc
Input Voltage (off) ($V_{CE} = 5.0\text{ V}, I_C = 100\ \mu\text{A}$)	$V_{i(off)}$	-	0.7	0.5	Vdc
Input Voltage (on) ($V_{CE} = 0.3\text{ V}, I_C = 1.0\text{ mA}$)	$V_{i(on)}$	1.4	0.8	-	Vdc
Output Voltage (on) ($V_{CC} = 5.0\text{ V}, V_B = 2.5\text{ V}, R_L = 1.0\text{ k}\Omega$)	V_{OL}	-	-	0.2	Vdc
Output Voltage (off) ($V_{CC} = 5.0\text{ V}, V_B = 0.5\text{ V}, R_L = 1.0\text{ k}\Omega$)	V_{OH}	4.9	-	-	Vdc
Input Resistor	R_1	7.0	10	13	k Ω
Resistor Ratio	R_1/R_2	0.17	0.21	0.25	

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

- Pulsed Condition: Pulse Width = 300 msec, Duty Cycle $\leq 2\%$.

TYPICAL CHARACTERISTICS
MUN2214, MMUN2214L, MUN5214, DTC114YE, DTC114YM3

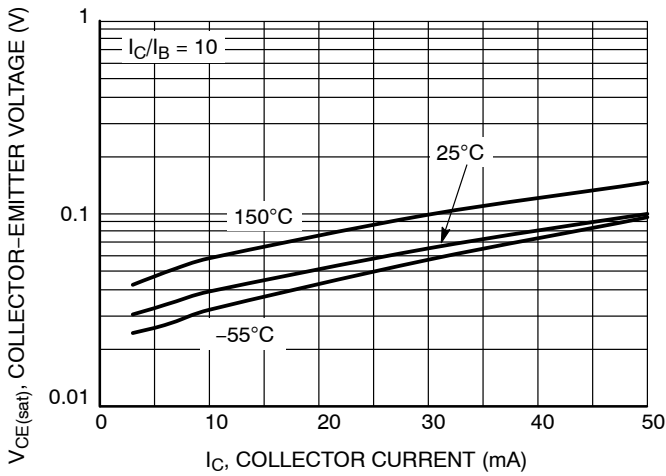


Figure 2. $V_{CE(sat)}$ vs. I_C

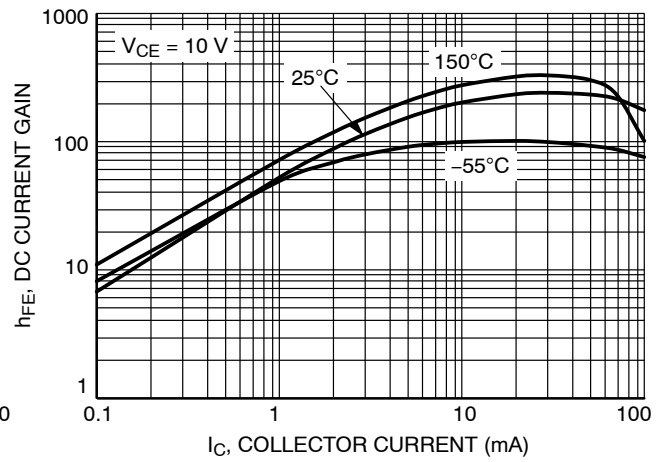


Figure 3. DC Current Gain

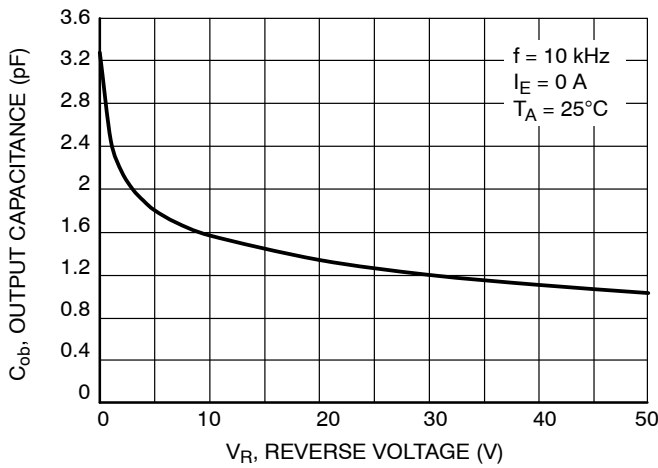


Figure 4. Output Capacitance

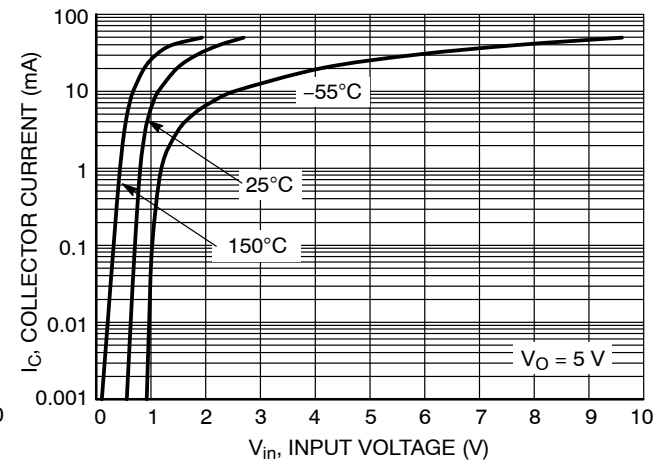


Figure 5. Output Current vs. Input Voltage

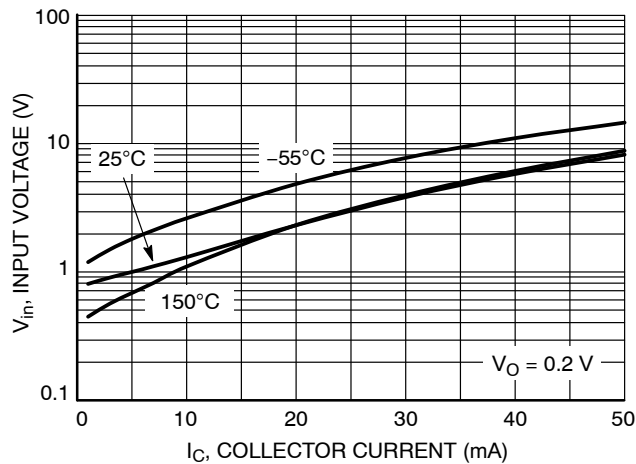


Figure 6. Input Voltage vs. Output Current

TYPICAL CHARACTERISTICS
NSBC114YF3

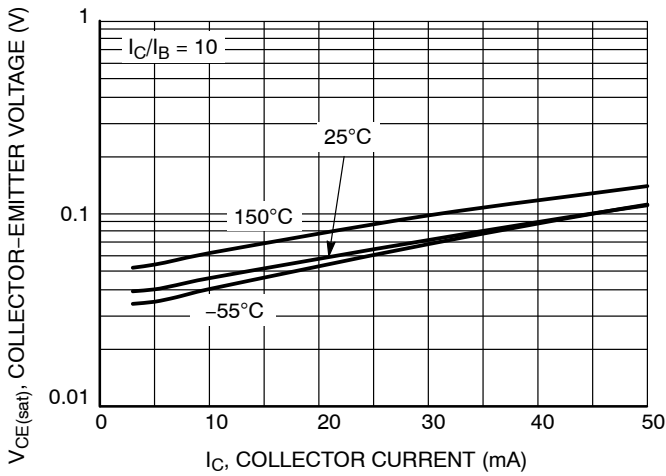


Figure 7. $V_{CE(sat)}$ vs. I_C

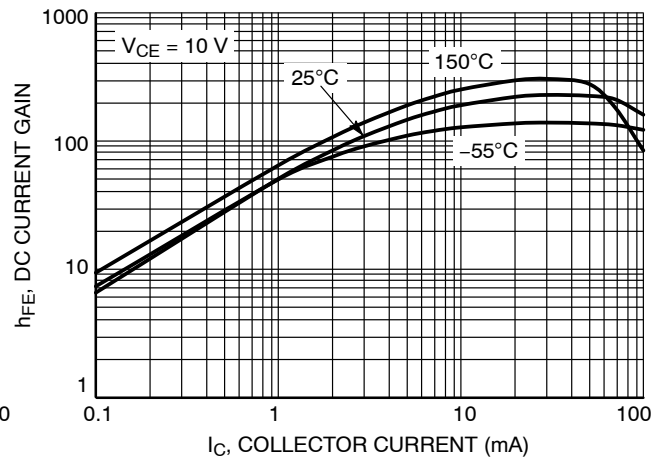


Figure 8. DC Current Gain

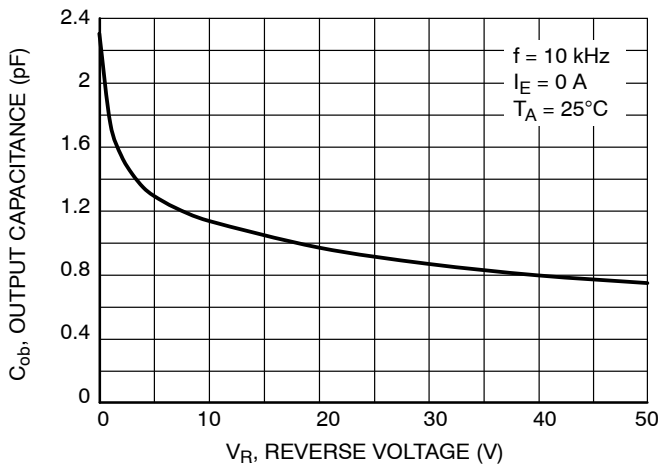


Figure 9. Output Capacitance

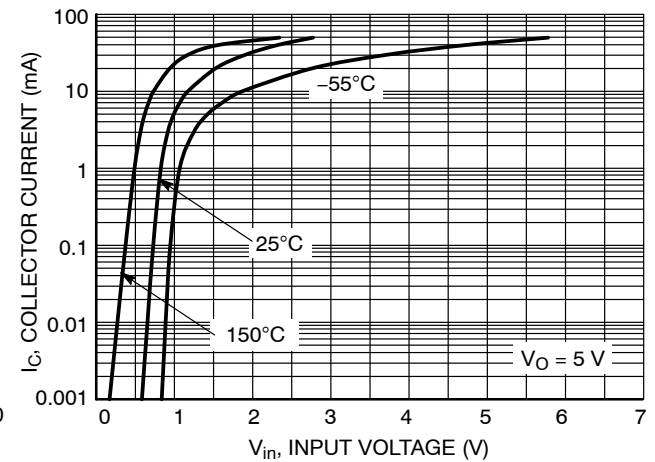


Figure 10. Output Current vs. Input Voltage

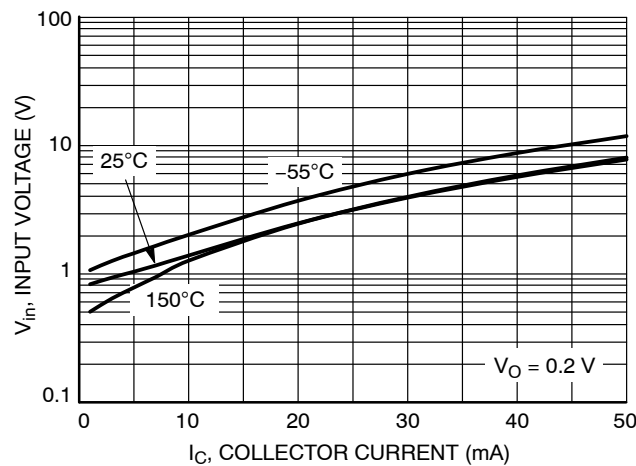


Figure 11. Input Voltage vs. Output Current

REVISION HISTORY

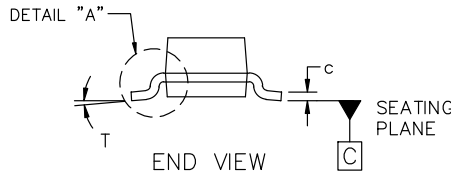
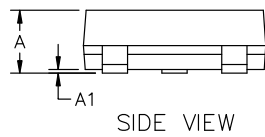
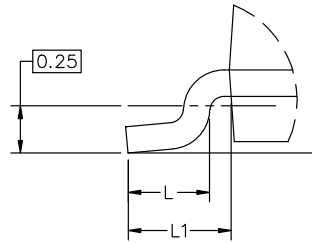
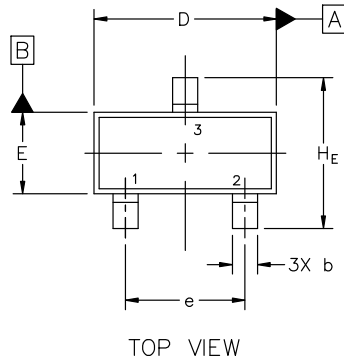
Revision	Description of Changes	Date
5	Rebranded the Data Sheet to onsemi format	5/28/2025



SCALE 4:1

SOT-23 (TO-236) 2.90x1.30x1.00 1.90P
CASE 318
ISSUE AU

DATE 14 AUG 2024

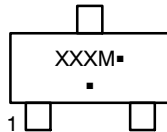


MILLIMETERS			
DIM	MIN	NOM	MAX
A	0.89	1.00	1.11
A1	0.01	0.06	0.10
b	0.37	0.44	0.50
c	0.08	0.14	0.20
D	2.80	2.90	3.04
E	1.20	1.30	1.40
e	1.78	1.90	2.04
L	0.30	0.43	0.55
L1	0.35	0.54	0.69
HE	2.10	2.40	2.64
T	0°	---	10°

NOTES:

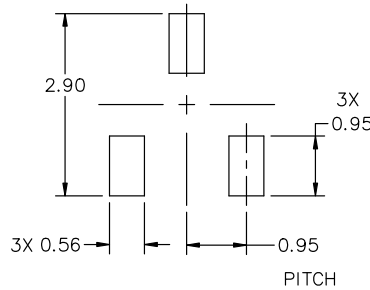
1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 2018.
2. CONTROLLING DIMENSIONS: MILLIMETERS.
3. MAXIMUM LEAD THICKNESS INCLUDES LEAD FINISH. MINIMUM LEAD THICKNESS IS THE MINIMUM THICKNESS OF THE BASE MATERIAL.
4. DIMENSIONS D AND E DO NOT INCLUDE MOLD FLASH, PROTRUSIONS, OR GATE BURRS.

GENERIC MARKING DIAGRAM*



XXX = Specific Device Code
M = Date Code
▪ = Pb-Free Package

*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot "▪", may or may not be present. Some products may not follow the Generic Marking.



* For additional information on our Pb-Free strategy and soldering details, please download the onsemi Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

STYLES ON PAGE 2

DOCUMENT NUMBER:	98ASB42226B	Electronic versions are uncontrolled except when accessed directly from the Document Repository. Printed versions are uncontrolled except when stamped "CONTROLLED COPY" in red.
DESCRIPTION:	SOT-23 (TO-236) 2.90x1.30x1.00 1.90P	PAGE 1 OF 2

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SOT-23 (TO-236) 2.90x1.30x1.00 1.90P
CASE 318
ISSUE AU

DATE 14 AUG 2024

STYLE 1 THRU 5:
CANCELLED

STYLE 6:
PIN 1. BASE
2. EMITTER
3. COLLECTOR

STYLE 7:
PIN 1. EMITTER
2. BASE
3. COLLECTOR

STYLE 8:
PIN 1. ANODE
2. NO CONNECTION
3. CATHODE

STYLE 9:
PIN 1. ANODE
2. ANODE
3. CATHODE

STYLE 10:
PIN 1. DRAIN
2. SOURCE
3. GATE

STYLE 11:
PIN 1. ANODE
2. CATHODE
3. CATHODE-ANODE

STYLE 12:
PIN 1. CATHODE
2. CATHODE
3. ANODE

STYLE 13:
PIN 1. SOURCE
2. DRAIN
3. GATE

STYLE 14:
PIN 1. CATHODE
2. GATE
3. ANODE

STYLE 15:
PIN 1. GATE
2. CATHODE
3. ANODE

STYLE 16:
PIN 1. ANODE
2. CATHODE
3. CATHODE

STYLE 17:
PIN 1. NO CONNECTION
2. ANODE
3. CATHODE

STYLE 18:
PIN 1. NO CONNECTION
2. CATHODE
3. ANODE

STYLE 19:
PIN 1. CATHODE
2. ANODE
3. CATHODE-ANODE

STYLE 20:
PIN 1. CATHODE
2. ANODE
3. GATE

STYLE 21:
PIN 1. GATE
2. SOURCE
3. DRAIN

STYLE 22:
PIN 1. RETURN
2. OUTPUT
3. INPUT

STYLE 23:
PIN 1. ANODE
2. ANODE
3. CATHODE

STYLE 24:
PIN 1. GATE
2. DRAIN
3. SOURCE

STYLE 25:
PIN 1. ANODE
2. CATHODE
3. GATE

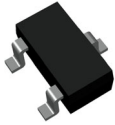
STYLE 26:
PIN 1. CATHODE
2. ANODE
3. NO CONNECTION

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2. CATHODE
3. CATHODE

STYLE 28:
PIN 1. ANODE
2. ANODE
3. ANODE

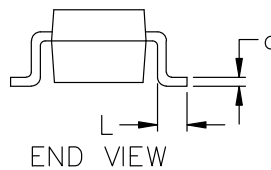
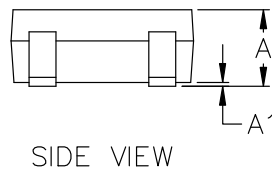
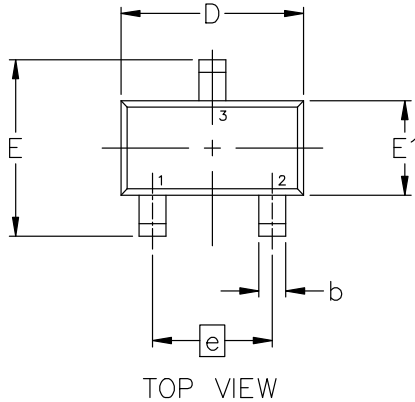
DOCUMENT NUMBER:	98ASB42226B	Electronic versions are uncontrolled except when accessed directly from the Document Repository. Printed versions are uncontrolled except when stamped "CONTROLLED COPY" in red.
DESCRIPTION:	SOT-23 (TO-236) 2.90x1.30x1.00 1.90P	PAGE 2 OF 2

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SC-59-3 2.90x1.50x1.15, 1.90P
CASE 318D
ISSUE J

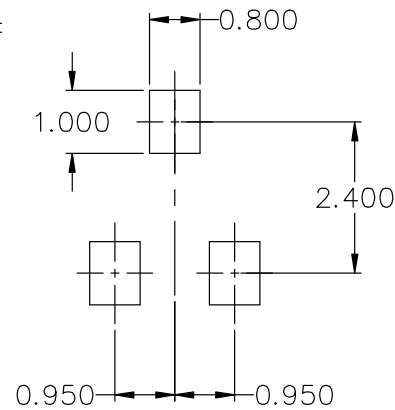
DATE 15 FEB 2024



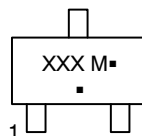
NOTES:

1. DIMENSIONING AND TOLERANCING CONFORM TO ASME Y14.5-2018.
2. ALL DIMENSION ARE IN MILLIMETERS.

DIM	MILLIMETERS		
	MIN.	NOM.	MAX.
A	1.00	1.15	1.30
A1	0.01	0.06	0.10
b	0.35	0.43	0.50
c	0.09	0.14	0.18
D	2.70	2.90	3.10
E	2.50	2.80	3.00
E1	1.30	1.50	1.70
e	1.90 BSC		
L	0.20	0.40	0.60



GENERIC MARKING DIAGRAM*



- XXX = Specific Device Code
- M = Date Code
- = Pb-Free Package*

(*Note: Microdot may be in either location)

*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot "▪", may or may not be present. Some products may not follow the Generic Marking.

* FOR ADDITIONAL INFORMATION ON OUR Pb-FREE STRATEGY AND SOLDERING DETAILS, PLEASE DOWNLOAD THE ON SEMICONDUCTOR SOLDERING AND MOUNTING TECHNIQUES REFERENCE MANUAL, SOLDERRM/D.

STYLE 1:
PIN 1. BASE
2. EMITTER
3. COLLECTOR

STYLE 2:
PIN 1. ANODE
2. N.C.
3. CATHODE

STYLE 3:
PIN 1. ANODE
2. ANODE
3. CATHODE

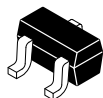
STYLE 4:
PIN 1. CATHODE
2. N.C.
3. ANODE

STYLE 5:
PIN 1. CATHODE
2. CATHODE
3. ANODE

STYLE 6:
PIN 1. ANODE
2. CATHODE
3. ANODE/CATHODE

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DESCRIPTION:	SC-59-3 2.90x1.50x1.15, 1.90P	PAGE 1 OF 1

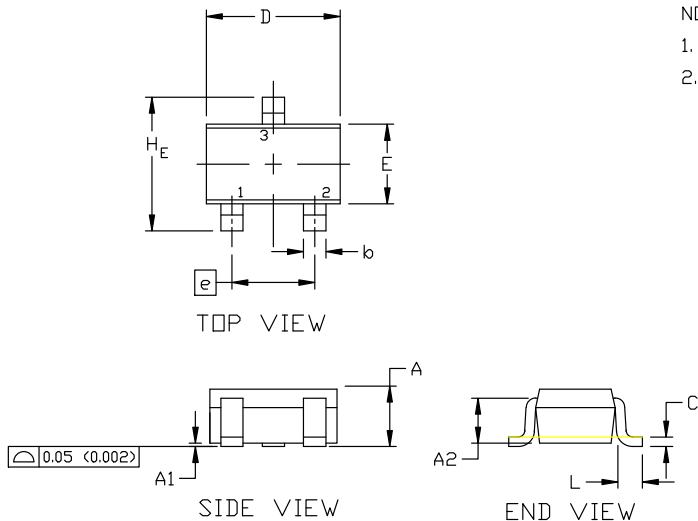
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SCALE 4:1

SC-70 (SOT-323)
CASE 419
ISSUE R

DATE 11 OCT 2022

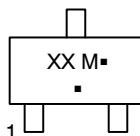


NOTES:

1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1982.
2. CONTROLLING DIMENSION: INCH

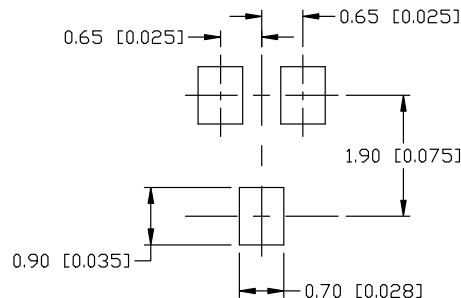
DIM	MILLIMETERS			INCHES		
	MIN.	NOM.	MAX.	MIN.	NOM.	MAX.
A	0.80	0.90	1.00	0.032	0.035	0.040
A1	0.00	0.05	0.10	0.000	0.002	0.004
A2	0.70 REF			0.028 BSC		
b	0.30	0.35	0.40	0.012	0.014	0.016
c	0.10	0.18	0.25	0.004	0.007	0.010
D	1.80	2.00	2.20	0.071	0.080	0.087
E	1.15	1.24	1.35	0.045	0.049	0.053
e	1.20	1.30	1.40	0.047	0.051	0.055
e1	0.65 BSC			0.026 BSC		
L	0.20	0.38	0.56	0.008	0.015	0.022
H _E	2.00	2.10	2.40	0.079	0.083	0.095

GENERIC
MARKING DIAGRAM



- XX = Specific Device Code
- M = Date Code
- = Pb-Free Package

*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot "▪", may or may not be present. Some products may not follow the Generic Marking.



* For additional information on our Pb-Free strategy and soldering details, please download the DN Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

SOLDERING FOOTPRINT

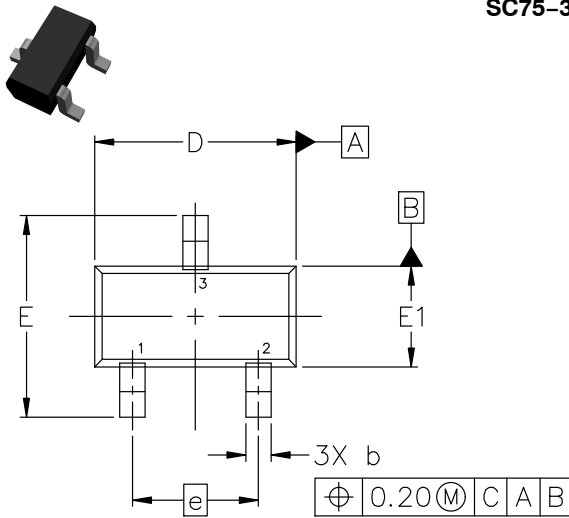
STYLE 1: CANCELLED	STYLE 2: PIN 1. ANODE 2. N.C. 3. CATHODE	STYLE 3: PIN 1. BASE 2. EMITTER 3. COLLECTOR	STYLE 4: PIN 1. CATHODE 2. CATHODE 3. ANODE	STYLE 5: PIN 1. ANODE 2. ANODE 3. CATHODE	
STYLE 6: PIN 1. EMITTER 2. BASE 3. COLLECTOR	STYLE 7: PIN 1. BASE 2. EMITTER 3. COLLECTOR	STYLE 8: PIN 1. GATE 2. SOURCE 3. DRAIN	STYLE 9: PIN 1. ANODE 2. CATHODE 3. CATHODE-ANODE	STYLE 10: PIN 1. CATHODE 2. ANODE 3. ANODE-CATHODE	STYLE 11: PIN 1. CATHODE 2. CATHODE 3. CATHODE

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DESCRIPTION:	SC-70 (SOT-323)	PAGE 1 OF 1

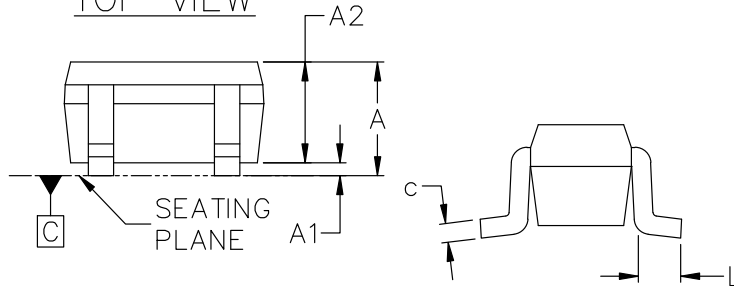
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SC75-3 1.60x0.80x0.80, 1.00P
CASE 463
ISSUE H

DATE 01 FEB 2024



TOP VIEW

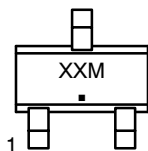


SIDE VIEW

END VIEW

DIM	MILLIMETERS		
	MIN.	NOM.	MAX.
A	0.70	0.80	0.90
A1	0.00	0.05	0.10
A2	0.80 REF.		
b	0.15	0.20	0.30
c	0.10	0.15	0.25
D	1.55	1.60	1.65
E	1.50	1.60	1.70
E1	0.70	0.80	0.90
e	1.00 BSC		
L	0.10	0.15	0.20

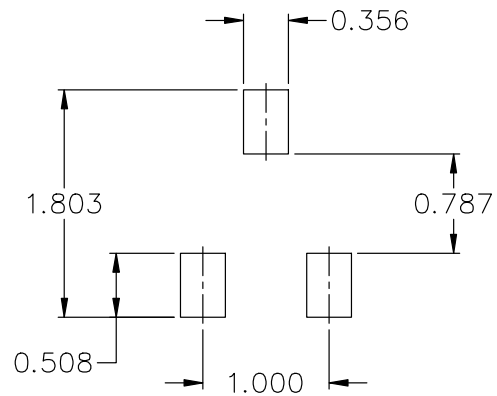
GENERIC MARKING DIAGRAM*



- XX = Specific Device Code
- M = Date Code
- = Pb-Free Package

*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot "▪", may or may not be present. Some products may not follow the Generic Marking.

- STYLE 1:
PIN 1. BASE
2. EMITTER
3. COLLECTOR
- STYLE 2:
PIN 1. ANODE
2. N/C
3. CATHODE
- STYLE 3:
PIN 1. ANODE
2. ANODE
3. CATHODE
- STYLE 4:
PIN 1. CATHODE
2. CATHODE
3. ANODE
- STYLE 5:
PIN 1. GATE
2. SOURCE
3. DRAIN

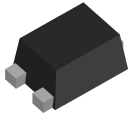


RECOMMENDED MOUNTING FOOTPRINT*

* FOR ADDITIONAL INFORMATION ON OUR Pb-FREE STRATEGY AND SOLDERING DETAILS, PLEASE DOWNLOAD THE ON SEMICONDUCTOR SOLDERING AND MOUNTING TECHNIQUES REFERENCE MANUAL, SOLDERRM/D.

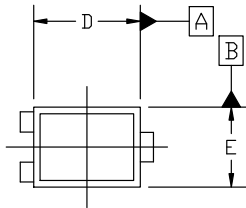
DOCUMENT NUMBER:	98ASB15184C	Electronic versions are uncontrolled except when accessed directly from the Document Repository. Printed versions are uncontrolled except when stamped "CONTROLLED COPY" in red.
DESCRIPTION:	SC75-3 1.60x0.80x0.80, 1.00P	PAGE 1 OF 1

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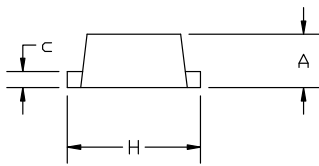


SOT-1123 0.80x0.60x0.37, 0.35P
CASE 524AA
ISSUE D

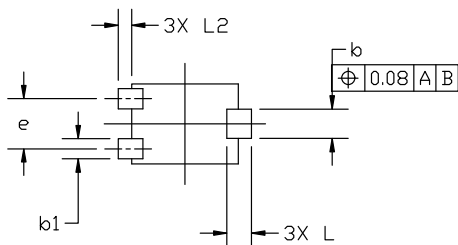
DATE 18 JAN 2024



TOP VIEW

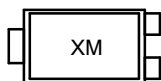


SIDE VIEW



BOTTOM VIEW

GENERIC MARKING DIAGRAM*



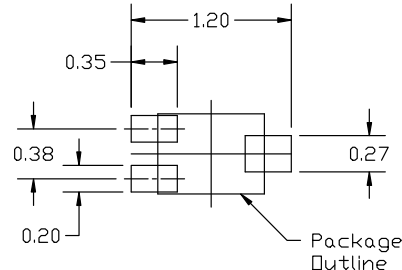
X = Specific Device Code
M = Date Code

*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot "•", may or may not be present. Some products may not follow the Generic Marking.

NOTES:

1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 2018.
2. CONTROLLING DIMENSION: MILLIMETERS.
3. MAXIMUM LEAD THICKNESS INCLUDES LEAD FINISH. MINIMUM LEAD THICKNESS IS THE MINIMUM THICKNESS OF BASE MATERIAL.
4. DIMENSIONS D AND E DO NOT INCLUDE MOLD FLASH, PROTRUSIONS, OR GATE BURRS.

MILLIMETERS			
DIM	MIN	NOM	MAX
A	0.34	0.37	0.40
b	0.15	0.22	0.28
b1	0.10	0.15	0.20
c	0.07	0.12	0.17
D	0.75	0.80	0.85
E	0.55	0.60	0.65
e	0.35	0.38	0.40
H	0.950	1.000	1.050
L	0.185 REF		
L2	0.05	0.10	0.15



RECOMMENDED MOUNTING FOOTPRINT

*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference manual, SOLDERM/D.

STYLE 1:
PIN 1. BASE
2. EMITTER
3. COLLECTOR

STYLE 2:
PIN 1. ANODE
2. N/C
3. CATHODE

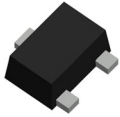
STYLE 3:
PIN 1. ANODE
2. ANODE
3. CATHODE

STYLE 4:
PIN 1. CATHODE
2. CATHODE
3. ANODE

STYLE 5:
PIN 1. GATE
2. SOURCE
3. DRAIN

DOCUMENT NUMBER:	98AON23134D	Electronic versions are uncontrolled except when accessed directly from the Document Repository. Printed versions are uncontrolled except when stamped "CONTROLLED COPY" in red.
DESCRIPTION:	SOT-1123 0.80x0.60x0.37, 0.35P	PAGE 1 OF 1

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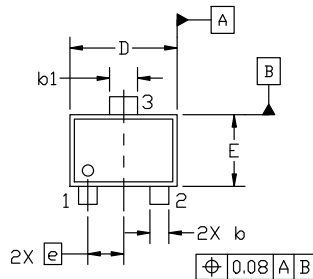
SOT-723 1.20x0.80x0.50, 0.40P
CASE 631AA
ISSUE E

DATE 24 JAN 2024

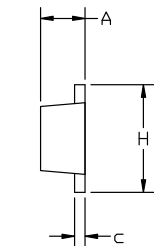
NOTES:

1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 2018.
2. CONTROLLING DIMENSION: MILLIMETERS.
3. MAXIMUM LEAD THICKNESS INCLUDES LEAD FINISH. MINIMUM LEAD THICKNESS IS THE MINIMUM THICKNESS OF BASE MATERIAL.
4. DIMENSIONS D AND E DO NOT INCLUDE MOLD FLASH, PROTRUSIONS OR GATE BURRS.

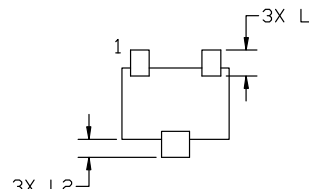
DIM	MILLIMETERS		
	MIN.	NOM.	MAX.
A	0.45	0.50	0.55
b	0.15	0.21	0.27
b1	0.25	0.31	0.37
c	0.07	0.12	0.17
D	1.15	1.20	1.25
E	0.75	0.80	0.85
e	0.40 BSC		
H	1.15	1.20	1.25
L	0.29 REF		
L2	0.15	0.20	0.25



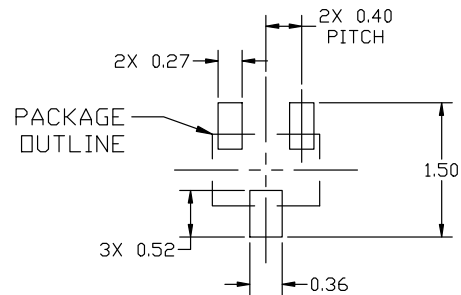
TOP VIEW



SIDE VIEW

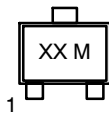


BOTTOM VIEW



RECOMMENDED MOUNTING FOOTPRINT

GENERIC MARKING DIAGRAM*



XX = Specific Device Code
M = Date Code

*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot "•", may or may not be present. Some products may not follow the Generic Marking.

*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERM/D.

STYLE 1: PIN 1. BASE 2. EMITTER 3. COLLECTOR	STYLE 2: PIN 1. ANODE 2. N/C 3. CATHODE	STYLE 3: PIN 1. ANODE 2. ANODE 3. CATHODE	STYLE 4: PIN 1. CATHODE 2. CATHODE 3. ANODE	STYLE 5: PIN 1. GATE 2. SOURCE 3. DRAIN
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DESCRIPTION:	SOT-723 1.20x0.80x0.50, 0.40P	PAGE 1 OF 1

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